

# NTLUS3A18PZ

## MOSFET – Power, Single, P-Channel, UDFN, 2.0x2.0x0.55 mm -20 V, -8.2 A



ON Semiconductor®

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### Features

- UDFN Package with Exposed Drain Pads for Excellent Thermal Conduction
- Low Profile UDFN 2.0x2.0x0.55 mm for Board Space Saving
- Ultra Low  $R_{DS(on)}$
- ESD Diode–Protected Gate
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

### Applications

- Optimized for Power Management Applications for Portable Products, such as Cell Phones, Media Tablets, PMP, DSC, GPS, and Others
- Battery Switch
- High Side Load Switch

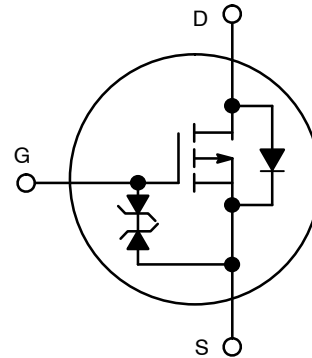
### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter		Symbol	Value	Unit	
Drain-to-Source Voltage		$V_{DSS}$	-20	V	
Gate-to-Source Voltage		$V_{GS}$	$\pm 8.0$	V	
Continuous Drain Current (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	$I_D$	-8.2	A
				$T_A = 85^\circ\text{C}$	
Continuous Drain Current (Note 1)	$t \leq 5 \text{ s}$	$T_A = 25^\circ\text{C}$	$I_D$	-12.2	A
Power Dissipation (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	$P_D$	1.7	W
				$t \leq 5 \text{ s}$	
Continuous Drain Current (Note 2)	Steady State	$T_A = 25^\circ\text{C}$	$I_D$	-5.1	A
		$T_A = 85^\circ\text{C}$		-3.7	
Power Dissipation (Note 2)		$T_A = 25^\circ\text{C}$	$P_D$	0.7	W
Pulsed Drain Current		$t_p = 10 \mu\text{s}$	$I_{DM}$	-25	A
Operating Junction and Storage Temperature		$T_J, T_{STG}$	-55 to 150	$^\circ\text{C}$	
ESD (HBM, JESD22-A114)		$V_{ESD}$	2000	V	
Source Current (Body Diode) (Note 2)		$I_S$	-1.7	A	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		$T_L$	260	$^\circ\text{C}$	

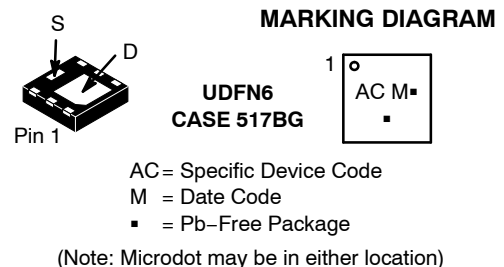
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Surface Mounted on FR4 Board using 1 in sq pad size (Cu area = 1.127 in sq [2 oz] including traces).
2. Surface-mounted on FR4 board using the minimum recommended pad size of 30 mm<sup>2</sup>, 2 oz. Cu.

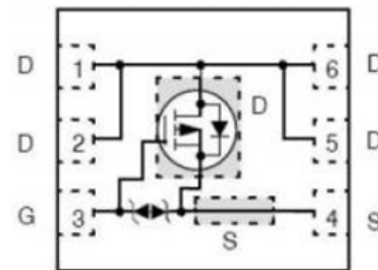
MOSFET		
$V_{(BR)DSS}$	$R_{DS(on)}$ MAX	$I_D$ MAX
-20 V	18 m $\Omega$ @ -4.5 V	-8.2 A
	25 m $\Omega$ @ -2.5 V	
	50 m $\Omega$ @ -1.8 V	
	90 m $\Omega$ @ -1.5 V	



P-Channel MOSFET



### PIN CONNECTIONS



(Top View)

### ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

# NTLUS3A18PZ

## THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Ambient – Steady State (Note 3)	$R_{\theta JA}$	72	°C/W
Junction-to-Ambient – $t \leq 5$ s (Note 3)	$R_{\theta JA}$	33	
Junction-to-Ambient – Steady State min Pad (Note 4)	$R_{\theta JA}$	189	

3. Surface-mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [2 oz] including traces).

4. Surface-mounted on FR4 board using the minimum recommended pad size of 30 mm<sup>2</sup>, 2 oz. Cu.

## ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
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### OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0$ V, $I_D = -250$ $\mu$ A	-20			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	$I_D = -250$ $\mu$ A, ref to $25^\circ\text{C}$		+10		mV/°C
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{GS} = 0$ V, $V_{DS} = -20$ V			-1.0	$\mu$ A
Gate-to-Source Leakage Current	$I_{GSS}$	$V_{DS} = 0$ V, $V_{GS} = \pm 5.0$ V			$\pm 5$	$\mu$ A

### ON CHARACTERISTICS (Note 5)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}$ , $I_D = -250$ $\mu$ A	-0.4		-1.0	V
Negative Threshold Temp. Coefficient	$V_{GS(TH)}/T_J$			3.0		mV/°C
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = -4.5$ V, $I_D = -7.0$ A		14.6	18	m $\Omega$
		$V_{GS} = -2.5$ V, $I_D = -5.0$ A		19	25	
		$V_{GS} = -1.8$ V, $I_D = -3.0$ A		25	50	
		$V_{GS} = -1.5$ V, $I_D = -1.0$ A		40	90	
Forward Transconductance	$g_{FS}$	$V_{DS} = -5$ V, $I_D = -3.0$ A		40		S

### CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	$C_{ISS}$	$V_{GS} = 0$ V, $f = 1$ MHz, $V_{DS} = -15$ V		2240		pF
Output Capacitance	$C_{OSS}$			240		
Reverse Transfer Capacitance	$C_{RSS}$			210		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = -4.5$ V, $V_{DS} = -15$ V; $I_D = -4.0$ A		28		nC
Threshold Gate Charge	$Q_{G(TH)}$			1.0		
Gate-to-Source Charge	$Q_{GS}$			2.9		
Gate-to-Drain Charge	$Q_{GD}$			8.8		

### SWITCHING CHARACTERISTICS, $V_{GS} = 4.5$ V (Note 6)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = -4.5$ V, $V_{DD} = -15$ V, $I_D = -4.0$ A, $R_G = 1$ $\Omega$		8.6		ns
Rise Time	$t_r$			15		
Turn-Off Delay Time	$t_{d(OFF)}$			150		
Fall Time	$t_f$			88		

### DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	$V_{SD}$	$V_{GS} = 0$ V, $I_S = -1.0$ A	$T_J = 25^\circ\text{C}$	0.63	1.0	V
			$T_J = 125^\circ\text{C}$	0.50		
Reverse Recovery Time	$t_{RR}$	$V_{GS} = 0$ V, $dI_S/dt = 100$ A/ $\mu$ s, $I_S = -1.0$ A		26.1		ns
Charge Time	$t_a$			10.2		
Discharge Time	$t_b$			15.9		
Reverse Recovery Charge	$Q_{RR}$			12		nC

5. Pulse Test: pulse width  $\leq 300$   $\mu$ s, duty cycle  $\leq 2\%$ .

6. Switching characteristics are independent of operating junction temperatures.

# NTLUS3A18PZ

## TYPICAL CHARACTERISTICS

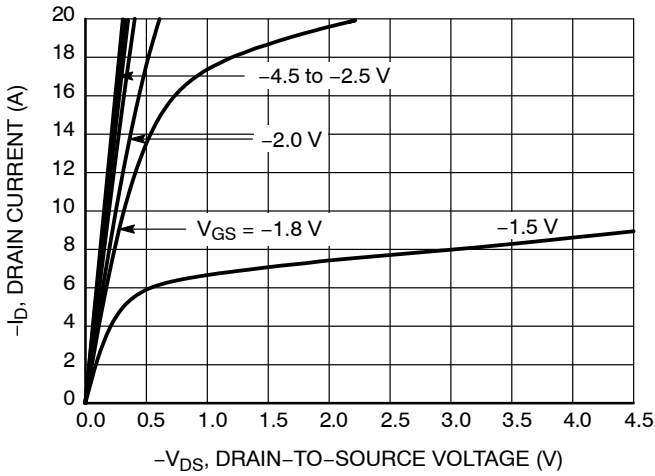


Figure 1. On-Region Characteristics

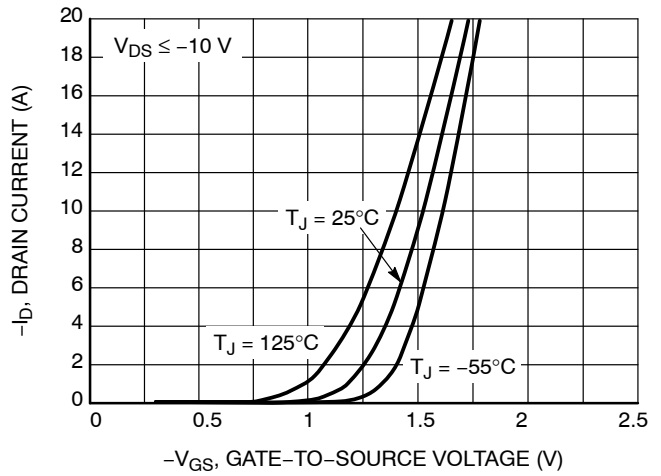


Figure 2. Transfer Characteristics

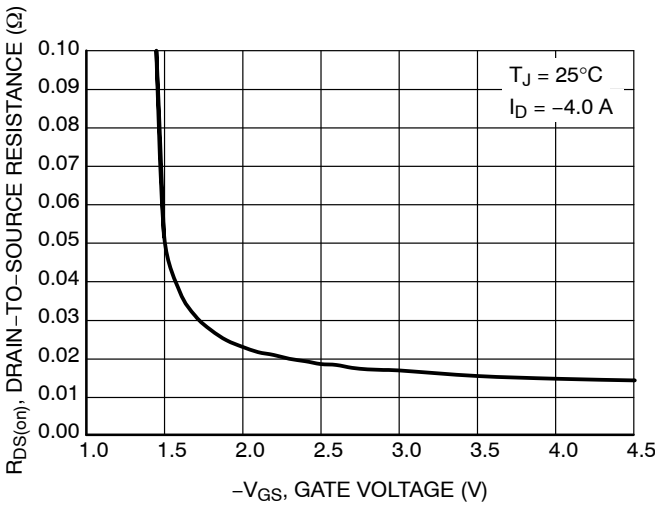


Figure 3. On-Resistance vs. Gate-to-Source Voltage

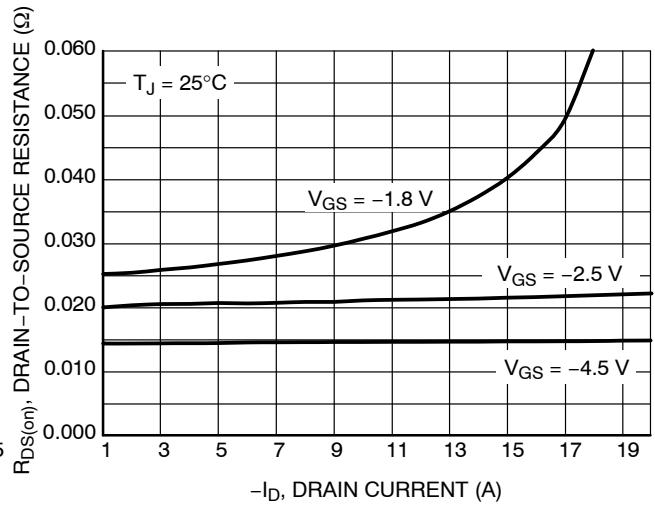


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

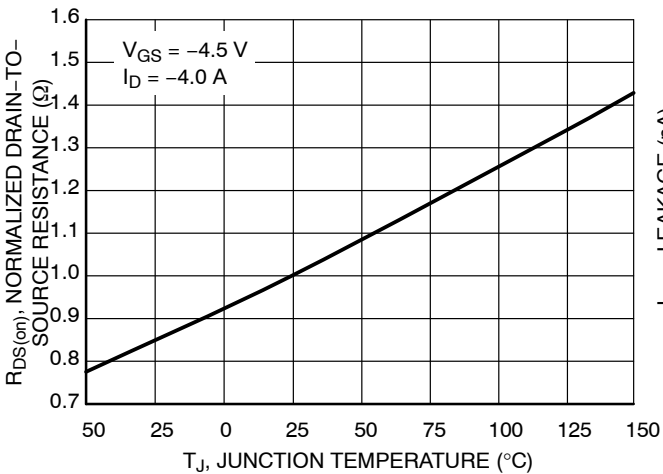


Figure 5. On-Resistance Variation with Temperature

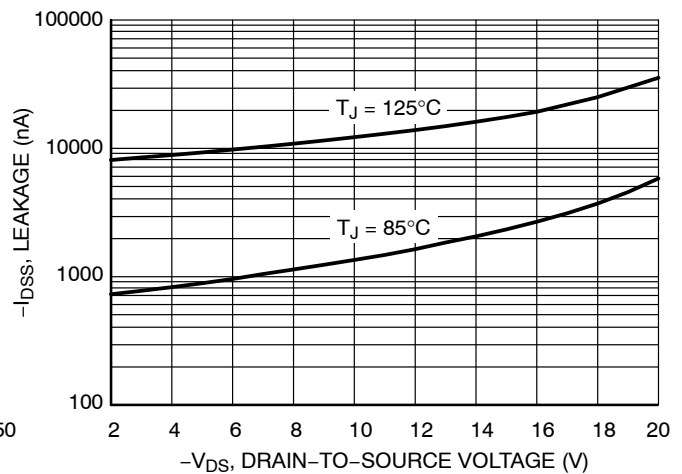


Figure 6. Drain-to-Source Leakage Current vs. Voltage

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## TYPICAL CHARACTERISTICS

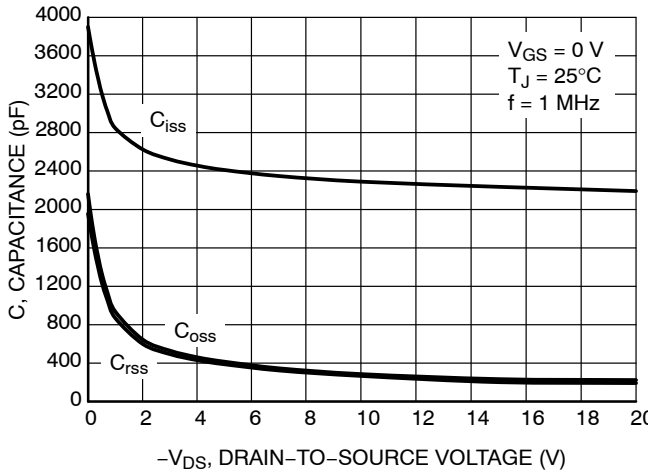


Figure 7. Capacitance Variation

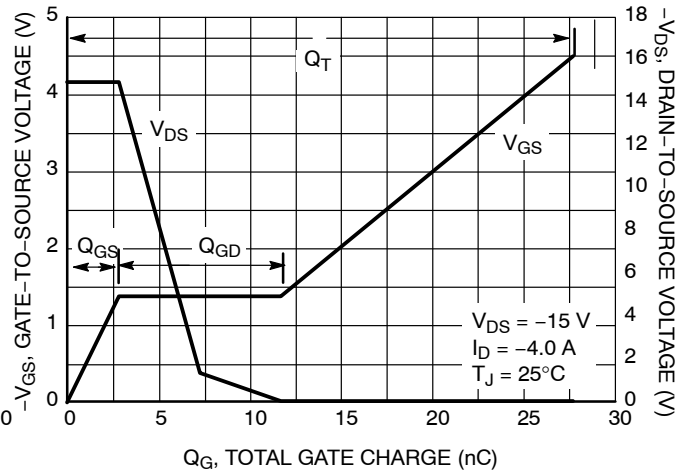


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

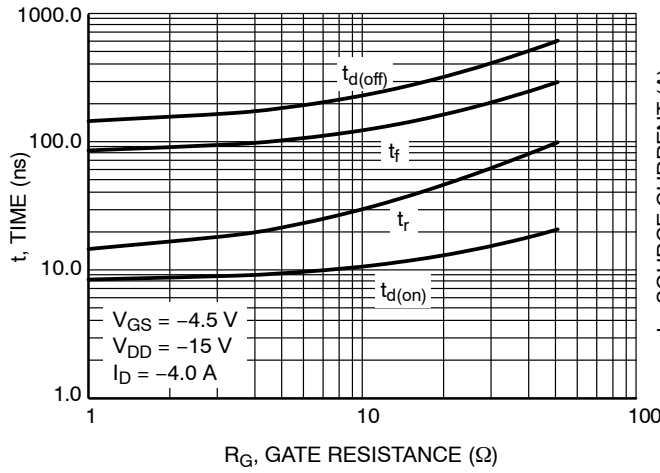


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

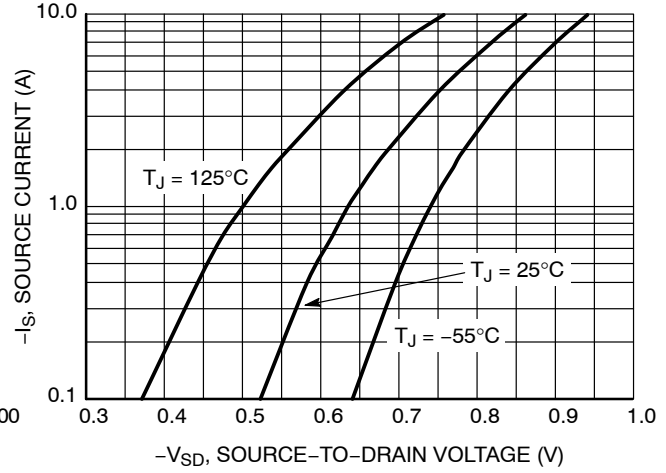


Figure 10. Diode Forward Voltage vs. Current

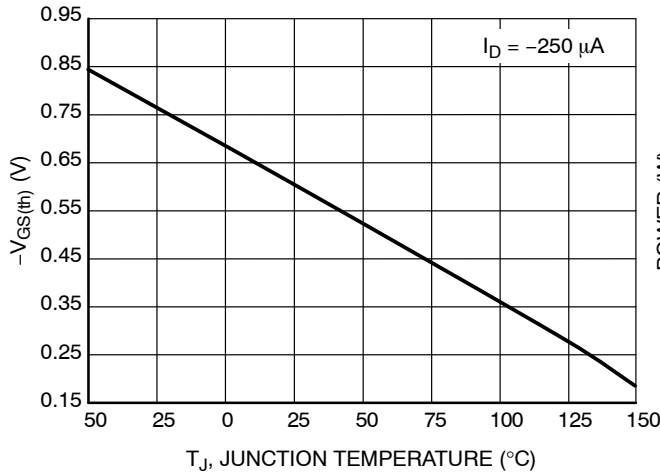


Figure 11. Threshold Voltage

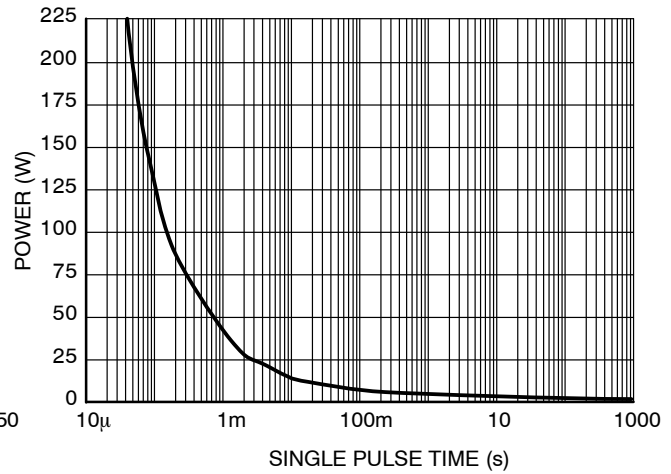
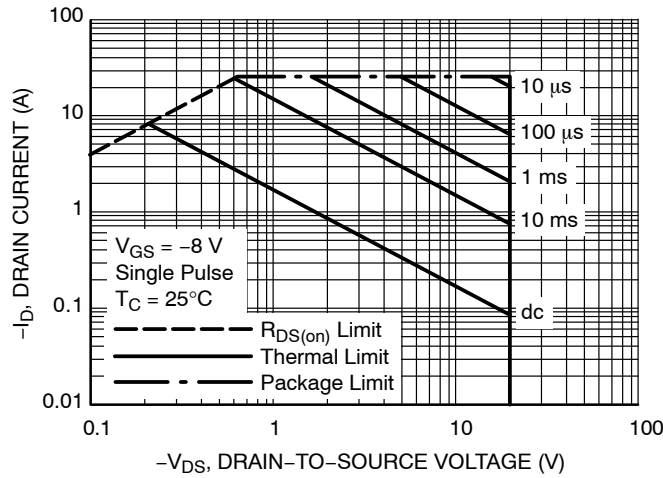


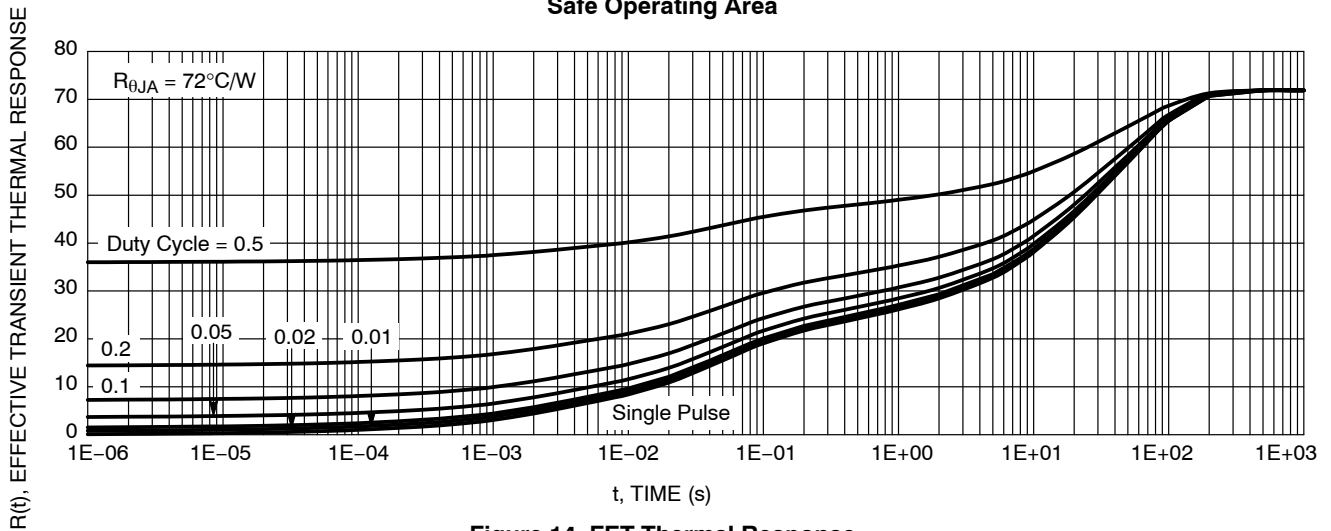
Figure 12. Single Pulse Maximum Power Dissipation

# NTLUS3A18PZ

## TYPICAL CHARACTERISTICS



**Figure 13. Maximum Rated Forward Biased Safe Operating Area**



**Figure 14. FET Thermal Response**

### DEVICE ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
NTLUS3A18PZTAG	UDFN6 (Pb-Free)	3000 / Tape & Reel
NTLUS3A18PZTBG	UDFN6 (Pb-Free)	3000 / Tape & Reel
NTLUS3A18PZTCG	UDFN6 (Pb-Free)	3000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

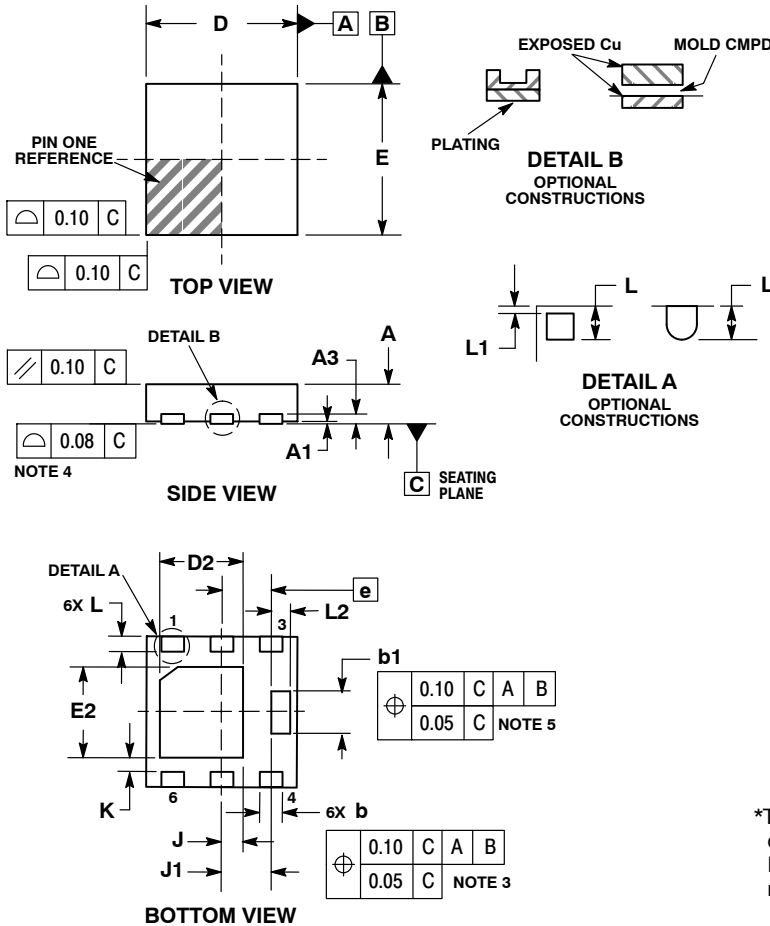
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SCALE 4:1

UDFN6 2x2, 0.65P  
CASE 517BG-01  
ISSUE A

DATE 04 FEB 2010



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30 mm FROM TERMINAL.
4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.
1. CENTER TERMINAL LEAD IS OPTIONAL. CENTER TERMINAL IS CONNECTED TO TERMINAL LEAD # 4.
2. LEADS 1, 2, 5 AND 6 ARE TIED TO THE FLAG.

DIM	MILLIMETERS	
	MIN	MAX
A	0.45	0.55
A1	0.00	0.05
A3	0.13 REF	
b	0.25	0.35
b1	0.51	0.61
D	2.00 BSC	
D2	1.00	1.20
E	2.00 BSC	
E2	1.10	1.30
e	0.65 BSC	
K	0.15 REF	
J	0.27 BSC	
J1	0.65 BSC	
L	0.20	0.30
L1	---	0.10
L2	0.20	0.30

### GENERIC MARKING DIAGRAM\*

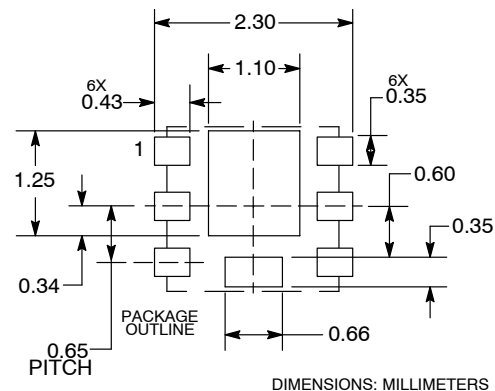


XX = Specific Device Code  
M = Date Code

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

### RECOMMENDED MOUNTING FOOTPRINT



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